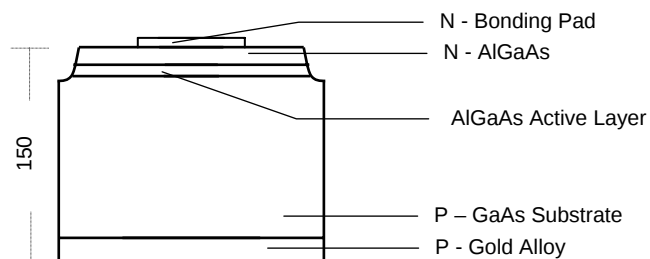
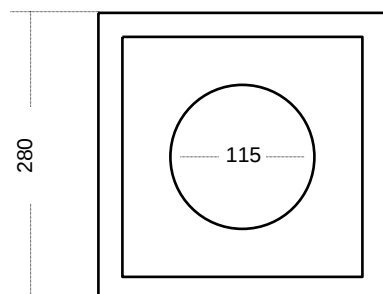


TCD660

❖ Outline Dimensions:

Unit: μm



❖ Physical Structure:

Chip dimensions	Chip size	12 mil x 12 mil	280 μm x 280 μm
	Thickness	6 mil	150 μm
	Bonding pad	4.5 mil	115 μm

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	-	2.00	V
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Peak Wavelength	λ_P	$I_F = 20\text{mA}$	645	-	675	nm
Spectral Bandwidth	$\Delta\lambda$	$I_F = 20\text{mA}$	-	30	-	nm
Output Power	P_O	$I_F = 20\text{mA}$	1.8	2.0	-	mW